



# Hybrid Power Module

## Integrated Power Stage for 2.0 hp Motor Drives

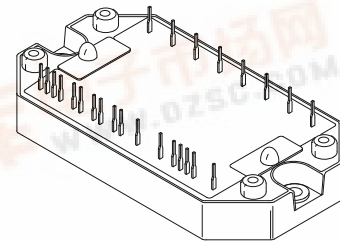
This module integrates a 3-phase input rectifier bridge, 3-phase output inverter and brake transistor/diode in a single convenient package. The output inverter utilizes advanced insulated gate bipolar transistors (IGBT) matched with free-wheeling diodes to give optimal dynamic performance. It has been configured for use as a three-phase motor drive module or for many other power switching applications. The top connector pins have been designed for easy interfacing to the user's control board.

- Short Circuit Rated 10  $\mu$ s @ 25°C
- Pin-to-Baseplate Isolation Exceeds 2500 Vac (rms)
- Convenient Package Outline
- UL  Recognized and Designed to Meet VDE 
- Access to Positive and Negative DC Bus

### MHPM7B12A120A

Motorola Preferred Device

**12 AMP, 1200 VOLT  
 HYBRID POWER MODULE**



PLASTIC PACKAGE  
 CASE 440-01, Style 1

#### MAXIMUM DEVICE RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
<b>INPUT RECTIFIER BRIDGE</b>			
Repetitive Peak Reverse Voltage	$V_{RRM}$	1200	V
Average Output Rectified Current (1)	$I_O$	12	A
Peak Non-repetitive Surge Current	$I_{FSM}$	200	A
<b>OUTPUT INVERTER</b>			
IGBT Reverse Voltage	$V_{CES}$	1200	V
Gate-Emitter Voltage	$V_{GES}$	$\pm 20$	V
Continuous IGBT Collector Current	$I_C$	12	A
Peak IGBT Collector Current – (PW = 1.0 ms) (2)	$I_{C(pk)}$	24	A
Continuous Free-Wheeling Diode Current	$I_F$	12	A
Peak Free-Wheeling Diode Current – (PW = 1.0 ms) (2)	$I_{F(pk)}$	24	A
IGBT Power Dissipation	$P_D$	60	W
Free-Wheeling Diode Power Dissipation	$P_D$	40	W
IGBT Junction Temperature Range	$T_J$	-40 to +125	$^\circ\text{C}$
Free-Wheeling Diode Junction Temperature Range	$T_J$	-40 to +125	$^\circ\text{C}$

(1) 1 cycle = 50 or 60 Hz

(2) 1 ms = 1.0% duty cycle

Preferred devices are Motorola recommended choices for future use and best overall value.



**MAXIMUM DEVICE RATINGS (continued)** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Rating	Symbol	Value	Unit
<b>BRAKE CIRCUIT</b>			
IGBT Reverse Voltage	$V_{CES}$	1200	V
Gate-Emitter Voltage	$V_{GES}$	$\pm 20$	V
Continuous IGBT Collector Current	$I_C$	12	A
Peak IGBT Collector Current (PW = 1.0 ms) (2)	$I_{C(pk)}$	24	A
IGBT Power Dissipation	PD	60	W
Diode Reverse Voltage	$V_{RRM}$	1200	V
Continuous Output Diode Current	$I_F$	12	A
Peak Output Diode Current (PW = 1.0 ms) (2)	$I_{F(pk)}$	24	A

**TOTAL MODULE**

Isolation Voltage – (47–63 Hz, 1.0 Minute Duration)	$V_{ISO}$	2500	VAC
Ambient Operating Temperature Range	$T_A$	- 40 to + 85	$^\circ\text{C}$
Operating Case Temperature Range	$T_C$	- 40 to + 90	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to +150	$^\circ\text{C}$
Mounting Torque	–	6.0	lb-in

**ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>INPUT RECTIFIER BRIDGE</b>					
Reverse Leakage Current ( $V_{RRM} = 1200\text{ V}$ )	$I_R$	–	10	50	$\mu\text{A}$
Forward Voltage ( $I_F = 12\text{ A}$ )	$V_F$	–	1.03	1.5	V
Thermal Resistance (Each Die)	$R_{\theta JC}$	–	–	2.9	$^\circ\text{C/W}$
<b>OUTPUT INVERTER</b>					
Gate-Emitter Leakage Current ( $V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$ )	$I_{GES}$	–	–	$\pm 20$	$\mu\text{A}$
Collector-Emitter Leakage Current ( $V_{CE} = 1200\text{ V}$ , $V_{GE} = 0\text{ V}$ ) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	$I_{CES}$	– –	– –	100 2.0	$\mu\text{A}$ mA
Gate-Emitter Threshold Voltage ( $V_{CE} = V_{GE}$ , $I_C = 1.0\text{ mA}$ )	$V_{GE(th)}$	4.0	6.0	8.0	V
Collector-Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $V_{GE} = 0$ )	$V_{(BR)CES}$	1200	1300	–	V
Collector-Emitter Saturation Voltage ( $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ )	$V_{CE(SAT)}$	–	2.4	3.5	V
Input Capacitance ( $V_{GE} = 0\text{ V}$ , $V_{CE} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{ies}$	–	1800	–	pF
Input Gate Charge ( $V_{CE} = 600\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ )	$Q_T$	–	65	–	nC
Fall Time – Inductive Load ( $V_{CE} = 600\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 150\ \Omega$ )	$t_{fi}$	–	300	500	ns
Turn-On Energy ( $V_{CE} = 600\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 150\ \Omega$ )	$E_{(on)}$	–	–	2.0	mJ
Turn-Off Energy ( $V_{CE} = 600\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 150\ \Omega$ )	$E_{(off)}$	–	–	2.0	mJ
Diode Forward Voltage ( $I_F = 12\text{ A}$ , $V_{GE} = 0\text{ V}$ )	$V_F$	–	1.7	2.2	V
Diode Reverse Recovery Time ( $I_F = 12\text{ A}$ , $V = 600\text{ V}$ , $di/dt = 100\text{ A}/\mu\text{s}$ )	$t_{rr}$	–	160	200	ns
Diode Stored Charge ( $I_F = 12\text{ A}$ , $V = 600\text{ V}$ , $di/dt = 100\text{ A}/\mu\text{s}$ )	$Q_{rr}$	–	800	950	nC
Thermal Resistance – IGBT (Each Die)	$R_{\theta JC}$	–	–	1.7	$^\circ\text{C/W}$
Thermal Resistance – Free-Wheeling Diode (Each Die)	$R_{\theta JC}$	–	–	2.7	$^\circ\text{C/W}$

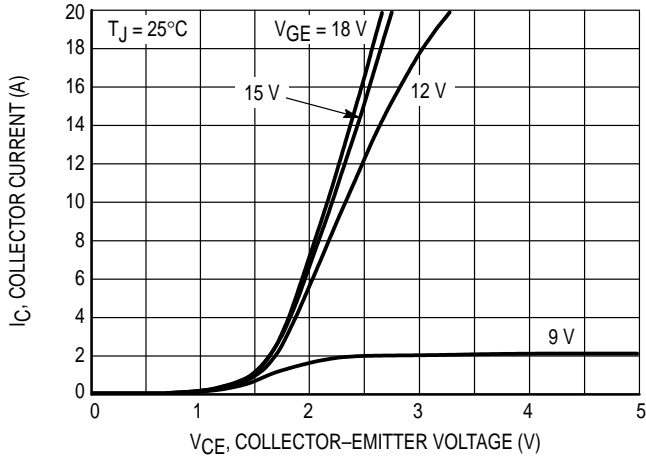
(2) 1.0 ms = 1.0% duty cycle

**ELECTRICAL CHARACTERISTICS (continued)** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

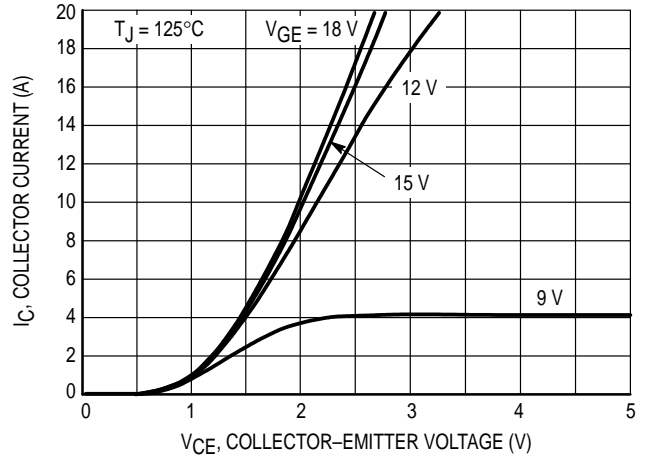
Characteristic	Symbol	Min	Typ	Max	Unit
<b>BRAKE CIRCUIT</b>					
Gate-Emitter Leakage Current ( $V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$ )	$I_{GES}$	–	–	$\pm 20$	$\mu\text{A}$
Collector-Emitter Leakage Current ( $V_{CE} = 1200\text{ V}$ , $V_{GE} = 0\text{ V}$ ) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	$I_{CES}$	– –	– –	100 2.0	$\mu\text{A}$ $\text{mA}$
Gate-Emitter Threshold Voltage ( $V_{CE} = V_{GE}$ , $I_C = 10\text{ mA}$ )	$V_{GE(th)}$	4.0	6.0	8.0	V
Collector-Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $V_{GE} = 0$ )	$V_{(BR)CES}$	1200	1300	–	V
Collector-Emitter Saturation Voltage ( $V_{GE} = 15\text{ V}$ , $I_C = 12\text{ A}$ )	$V_{CE(SAT)}$	–	2.4	3.5	V
Input Capacitance ( $V_{GE} = 0\text{ V}$ , $V_{CE} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{ies}$	–	1800	–	pF
Input Gate Charge ( $V_{CE} = 600\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ )	$Q_T$	–	65	–	nC
Fall Time – Inductive Load ( $V_{CE} = 600\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 150\ \Omega$ )	$t_{fi}$	–	300	500	ns
Turn-On Energy ( $V_{CE} = 600\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 150\ \Omega$ )	$E_{(on)}$	–	–	2.0	mJ
Turn-Off Energy ( $V_{CE} = 600\text{ V}$ , $I_C = 12\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 150\ \Omega$ )	$E_{(off)}$	–	–	2.0	mJ
Diode Forward Voltage ( $I_F = 12\text{ A}$ )	$V_F$	–	1.7	2.2	V
Diode Reverse Leakage Current	$I_R$	–	–	50	$\mu\text{A}$
Thermal Resistance – IGBT	$R_{\theta JC}$	–	–	1.7	$^\circ\text{C/W}$
Thermal Resistance – Diode	$R_{\theta JC}$	–	–	2.7	$^\circ\text{C/W}$



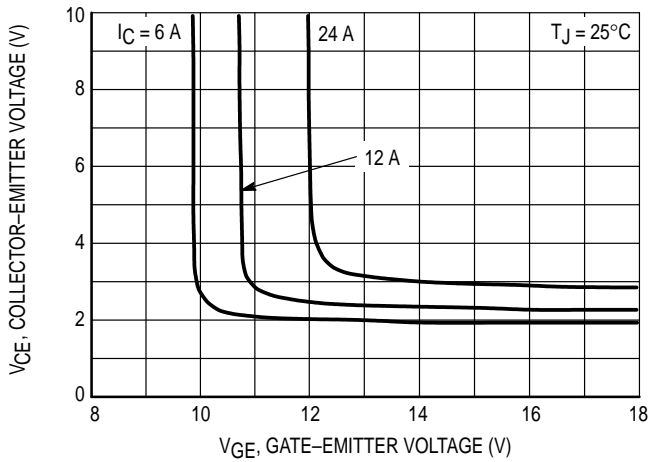
## Typical Characteristics



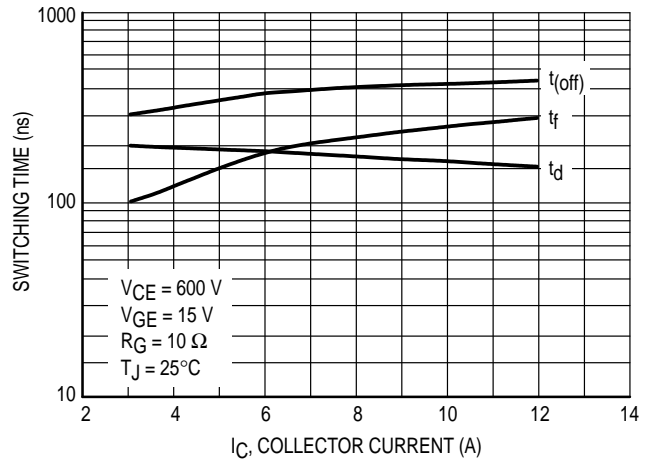
**Figure 2. Output Inverter Collector Current  $I_C$  versus Collector-Emitter Voltage  $V_{CE}$**



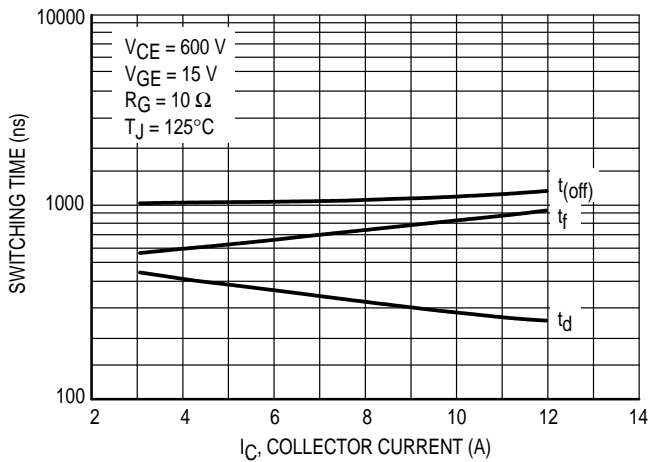
**Figure 3. Output Inverter Collector Current  $I_C$  versus Collector-Emitter Voltage  $V_{CE}$**



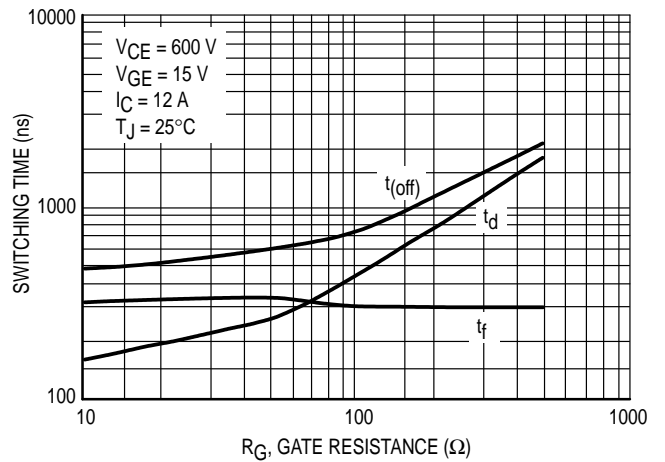
**Figure 4. Inverter Collector-Emitter Voltage  $V_{CE}$  versus Gate-Emitter Voltage  $V_{GE}$**



**Figure 5. Inverter Switching Time  $t_d$ ,  $t_f$ ,  $t_{(off)}$  versus Collector Current  $I_C$**

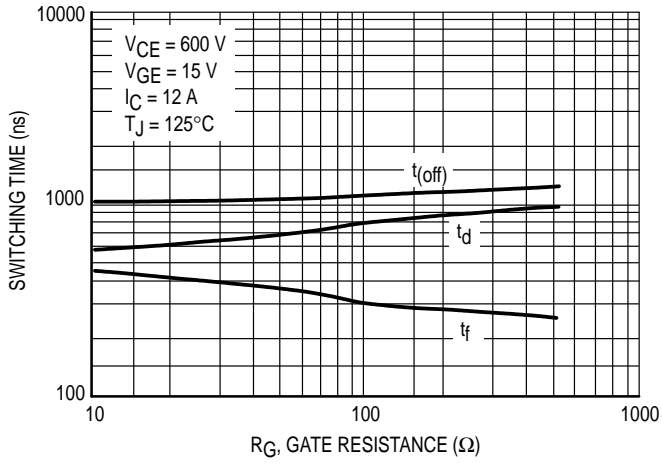


**Figure 6. Inverter Switching Time  $t_d$ ,  $t_f$ ,  $t_{(off)}$  versus Collector Current  $I_C$**

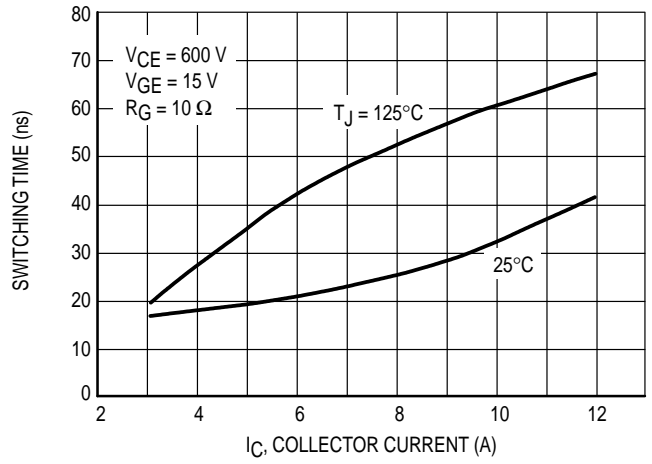


**Figure 7. Inverter Switching Time  $t_d$ ,  $t_f$ ,  $t_{(off)}$  versus Gate Resistance  $R_G$**

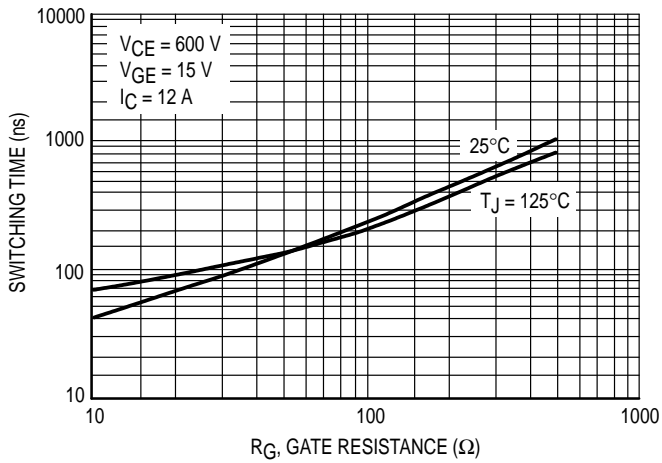
## Typical Characteristics



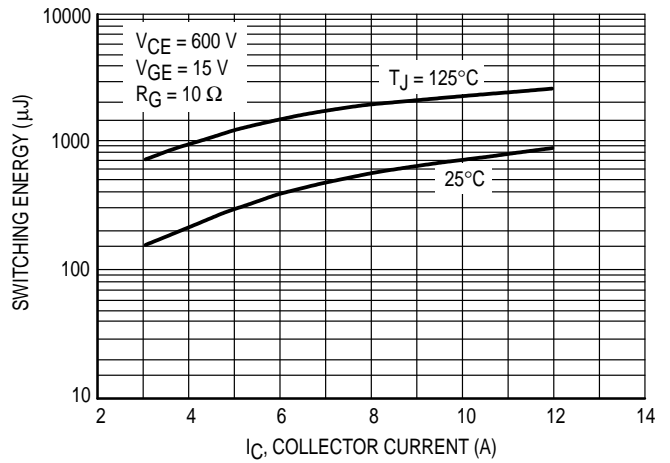
**Figure 8. Inverter Switching Time  $t_d$ ,  $t_f$ ,  $t_{(off)}$  versus Gate Resistance  $R_G$**



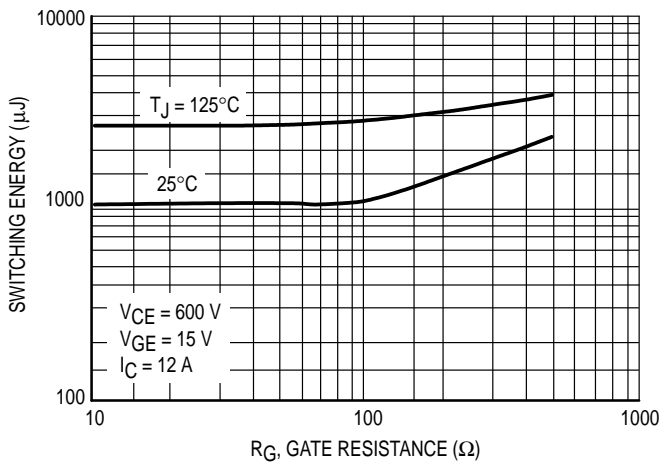
**Figure 9. Inverter Switching Time  $t_f$  versus Collector Current  $I_C$**



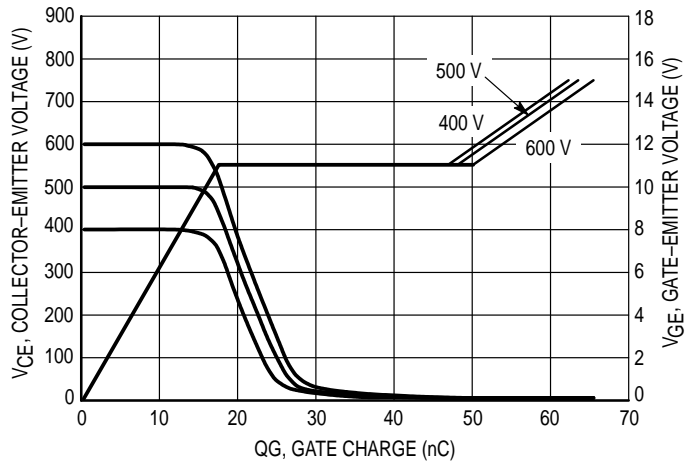
**Figure 10. Inverter Switching Time  $t_r$  versus Gate Resistance  $R_G$**



**Figure 11. Inverter Switching Energy  $E_{(off)}$  versus Collector Current  $I_C$**

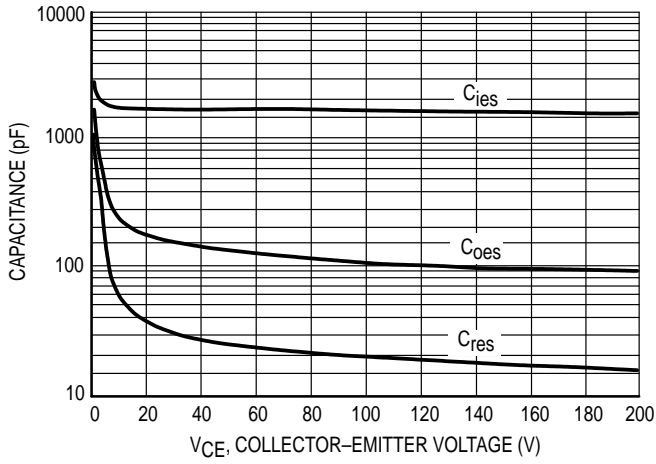


**Figure 12. Inverter Switching Energy  $E_{(off)}$  versus Gate Resistance  $R_G$**

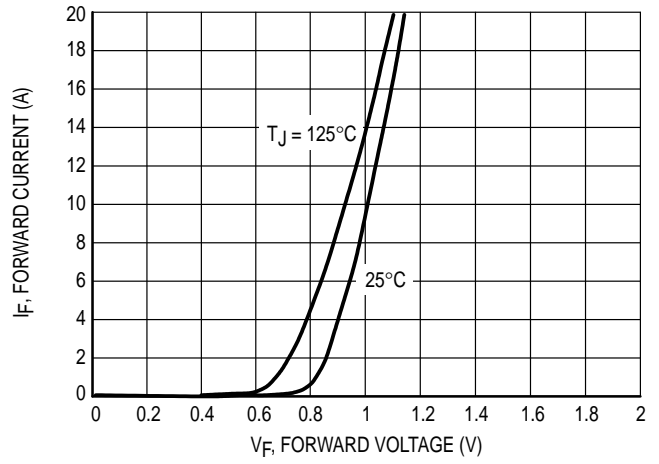


**Figure 13. Gate-to-Emitter Voltage versus Gate Charge**

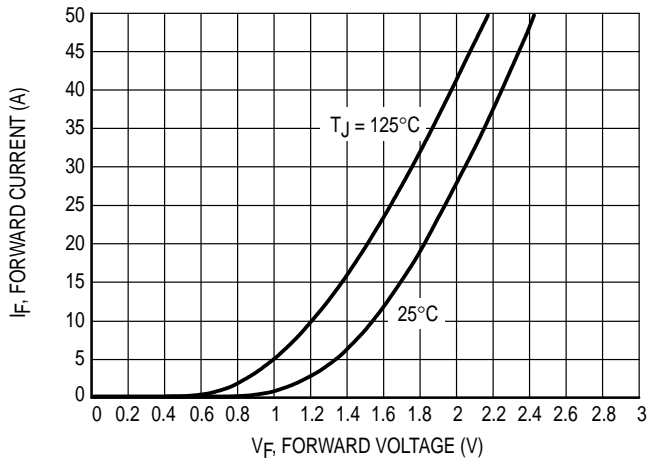
## Typical Characteristics



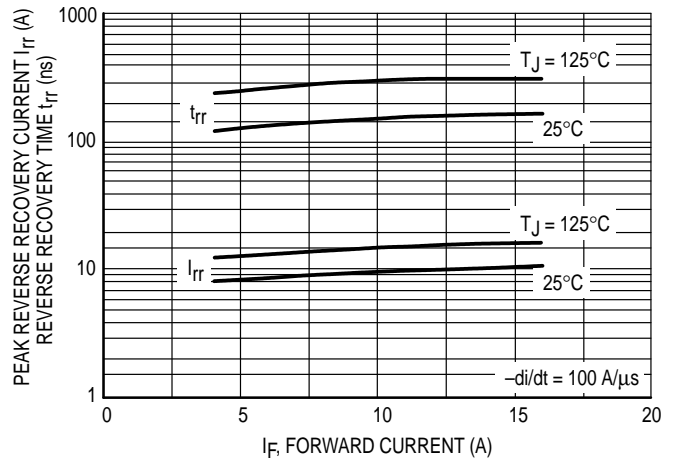
**Figure 14. Output Inverter Capacitance versus Collector Voltage  $V_{CE}$**



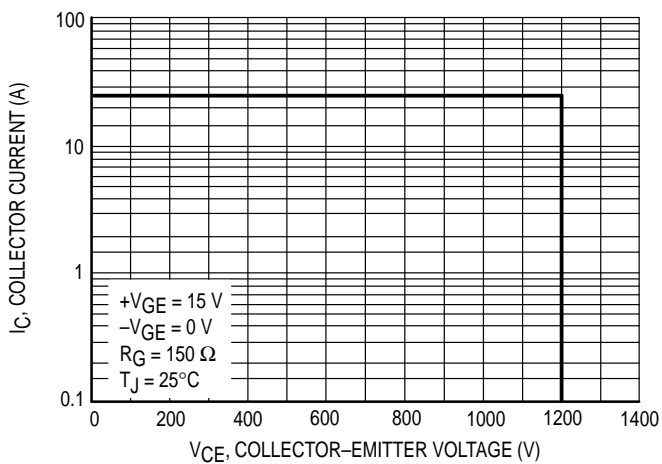
**Figure 15. Input Bridge Forward Current  $I_F$  versus Forward Voltage  $V_F$**



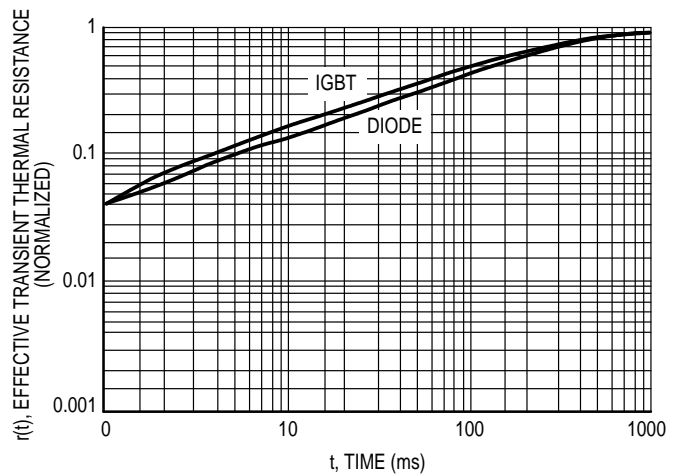
**Figure 16. Output Inverter Forward Current  $I_F$  versus Forward Voltage  $V_F$**



**Figure 17. Output Inverter Reverse Recovery  $t_{rr}$ ,  $I_{rr}$  versus Forward Current  $I_F$**

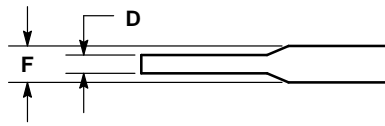
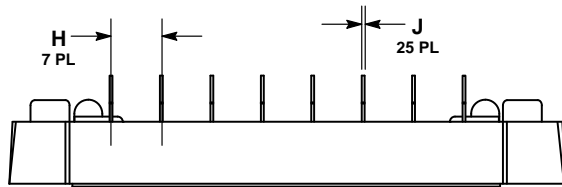
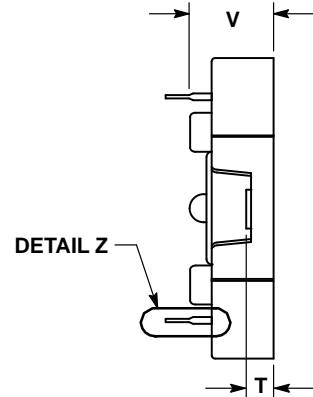
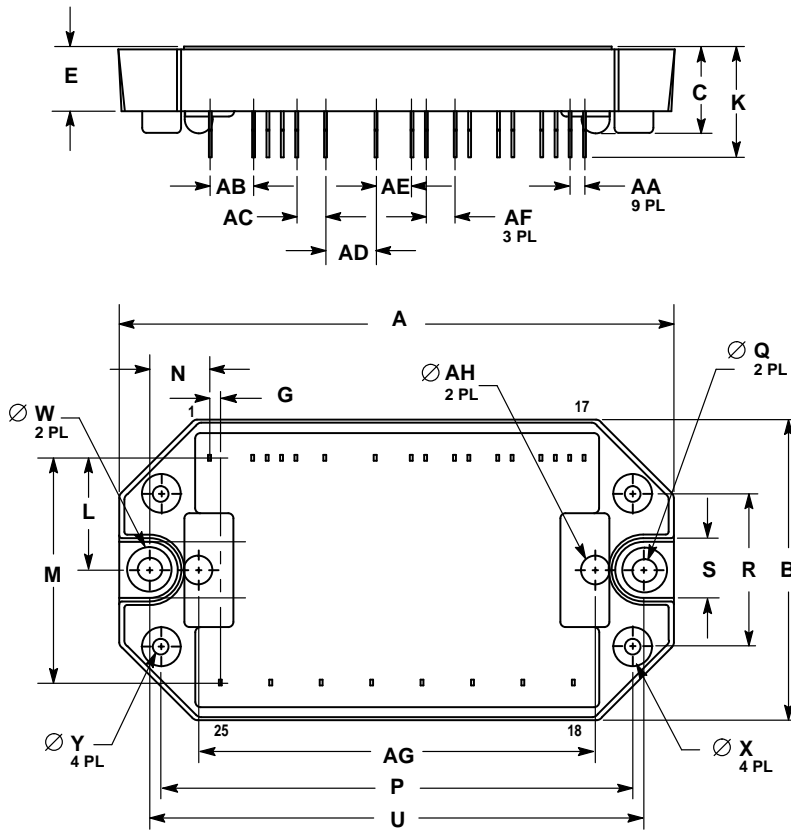


**Figure 18. Output Inverter Reversed Biased Safe Operating Area**



**Figure 19. Transient Thermal Resistance**

# PACKAGE DIMENSIONS




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. LEAD LOCATION DIMENSIONS (ie: M, B, AA...) ARE TO THE CENTER OF THE LEAD.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	97.54	98.55	3.840	3.880
B	52.45	53.47	2.065	2.105
C	14.60	15.88	0.575	0.625
D	0.43	0.84	0.017	0.033
E	10.80	12.06	0.425	0.475
F	0.94	1.35	0.037	0.053
G	1.60	2.21	0.063	0.087
H	8.58	9.19	0.338	0.362
J	0.30	0.71	0.012	0.028
K	18.80	20.57	0.74	0.81
L	19.30	20.32	0.760	0.800
M	38.99	40.26	1.535	1.585
N	9.78	11.05	0.385	0.435
P	82.55	83.57	3.250	3.290
Q	4.01	4.62	0.158	0.182
R	26.42	27.43	1.040	1.080
S	12.06	12.95	0.475	0.515
T	4.32	5.33	0.170	0.210
U	86.36	87.38	3.400	3.440
V	14.22	15.24	0.560	0.600
W	7.62	8.13	0.300	0.320
X	6.55	7.16	0.258	0.282
Y	2.49	3.10	0.098	0.122
AA	2.24	2.84	0.088	0.112
AB	7.32	7.92	0.288	0.312
AC	4.78	5.38	0.188	0.212
AD	8.58	9.19	0.338	0.362
AE	6.05	6.65	0.238	0.262
AF	4.78	5.38	0.188	0.212
AG	69.34	70.36	2.730	2.770
AH	—	5.08	—	0.200

- STYLE 1:
- |           |           |            |            |           |
|-----------|-----------|------------|------------|-----------|
| PIN 1. P1 | PIN 6. N2 | PIN 11. G3 | PIN 16. G2 | PIN 21. B |
| 2. T-     | 7. P2     | 12. K5     | 17. G4     | 22. T     |
| 3. T+     | 8. K1     | 13. G5     | 18. W      | 23. S     |
| 4. I+     | 9. G1     | 14. G6     | 19. V      | 24. R     |
| 5. I-     | 10. K3    | 15. G7     | 20. U      | 25. N1    |

CASE 440-01  
ISSUE O



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